



September 2015

KSP42 / KSP43 NPN Epitaxial Silicon Transistor

Features

- Collector-Emitter Voltage: V_{CEO} = KSP42: 300 V
KSP43: 200 V
- Collector Dissipation: P_C (max.) = 625 mW



Ordering Information

Part Number	Top Mark	Package	Packing Method
KSP42BU	KSP42	TO-92 3L	Bulk
KSP42TA	KSP42	TO-92 3L	Ammo
KSP43BU	KSP43	TO-92 3L	Bulk
KSP43TA	KSP43	TO-92 3L	Ammo

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	KSP42	300
		KSP43	200
V_{CEO}	Collector-Emitter Voltage	KSP42	300
		KSP43	200
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	500	mA
P_C	Collector Power Dissipation	625	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55 to 150	$^\circ\text{C}$